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CONTENTS

Effect of tin addition on primary silicon recovery in Si–Al melt during solidification refining of silicon J. Li, Y. Liu, Y. Tan, Y. Li, L. Zhang, S. Wu and P. Jia	1	Global simulation of the Czochralski silicon crystal growth in ANSYS FLUENT M. Kirpo	60
Hillock formation and suppression on <i>c</i> -plane homoepitaxial GaN Layers grown by metalorganic vapor phase epitaxy K. Zhou, J. Liu, S. Zhang, Z. Li, M. Feng, D. Li, L. Zhang, F. Wang, J. Zhu and H. Yang	7	REECOB: 20 years of rare earth element calcium oxoborates crystal growth research R. Möckel, C. Reuther and J. Götz	70
Phase control of semi-polar (11 $\bar{2}$ 2) and non-polar (1120) GaN on cone shaped <i>r</i> -plane patterned sapphire substrates M.-T. Wang, F. Brunner, K.-Y. Liao, Y.-L. Li, S.H. Tseng and M. Weyers	11	Surface tension of liquid silicon: High or low value? N. Eustathopoulos and B. Drevet	77
Cycloid crystals by topology change T. Matsuura, T. Matsuyama and S. Tanda	17	Inclusion behavior of Cs, Sr, and Ba impurities in LiCl crystal formed by layer-melt crystallization: Combined first-principles calculation and experimental study J.-H. Choi, Y.-Z. Cho, T.-K. Lee, H.-C. Eun, J.-H. Kim, I.-T. Kim, G.-I. Park and J.-K. Kang	84
Vapor–liquid–solid growth of thick 2H–SiC layers under CH ₄ continuous flow Y. Nakagawa, S. Takeuchi, A. Ishikawa, M. Imade, M. Yoshimura and Y. Mori	23	On thermal conditions and properties of thallium bromide single crystals grown by the Electro Dynamic Gradient method Z. Zheng, Y. Yu, S. Gong, Q. Fu and D. Zhou	90
Growth and characterization of low yttria-doped fully cubic stabilized zirconia-based single crystals S. Berendts and M. Lerch	28	Basal plane dislocation conversion near the epilayer/substrate interface in epitaxial growth of 4° off-axis 4H–SiC H. Song and T.S. Sudarshan	94
High surface area calcite L.N. Schultz, M.P. Andersson, K.N. Dalby, D. Müter, D.V. Okhrimenko, H. Fordsmand and S.L.S. Stipp	34	The role of alkali additives in the crystallization of ferroelectric potassium lithium niobate crystals Á. Péter, I. Hajdara, Zs. Szaller, K. Lengyel and L. Kovács	102
Controlling structural properties of positioned quantum dots M. Helfrich, B. Terhalle, Y. Ekinici and D.M. Schaadt	39	<i>In-situ</i> study on growth units of Ba ₂ Mg(B ₃ O ₆) ₂ crystal X.S. Lv, Y.L. Sun, X.L. Tang, S.M. Wan, Q.L. Zhang, J.L. You and S.T. Yin	107
Impact of AlN nucleation layer on strain in GaN grown on 4H–SiC substrates E. Cho, A. Mogilatenko, F. Brunner, E. Richter and M. Weyers	45	Crystal growth and scintillation properties of CsCaBr ₃ :Eu ²⁺ (CsCa _{1-x} Eu _x Br ₃ , 0 ≤ x ≤ 0.08) A.Yu. Grippa, N.V. Rebrova, T.E. Gorbacheva, V.Yu. Pedash, N.N. Kosinov, V.L. Cherginets, V.A. Tarasov, O.A. Tarasenko and A.V. Lopin	112
In-rich molecular beam epitaxy of InAs on Sb-terminated GaAs(001) surface A.V. Katkov, C.C. Wang and J.Y. Chi	50	Time evolution of self-assembled GaAs quantum rings grown by droplet epitaxy K.H.P. Tung, H.W. Gao and N. Xiang	117
Base-growth mechanism of double-walled carbon nanotube in chemical vapor deposition H. Shahrokhbadi, M. Saeidi, M. Vaezzadeh, H. Shahivandi and M. Salehian	56	GaSb/ZnTe double-heterostructures grown using molecular beam epitaxy J. Fan, L. Ouyang, X. Liu, J.K. Furdyna, D.J. Smith and Y.-H. Zhang	122

Contents continued on inside back cover



Microstructure and optical properties of Fe-doped ZnO thin films prepared by DC magnetron sputtering F. Gao, X.Y. Liu, L.Y. Zheng, M.X. Li, Y.M. Bai and J. Xie	126	Misorientation defects in coalesced self-catalyzed GaN nanowires K.A. Grossklous, A. Banerjee, S. Jahangir, P. Bhattacharya and J.M. Millunchick	142
Mismatch and thermal strain analysis in MBE-grown HgCdTe/CdZnTe P. Ballet, A. Jonchère, B. Amstatt, X. Baudry, B. Polge, D. Brellier and P. Gergaud	130	InP nanowires synthesized via solvothermal process with CTAB assisted Y. Zhao, Y. Yu and F. Gao	148
Silicon optical fiber diameter dependent grain size B.L. Scott and G.R. Pickrell	134	State of the art of the heavy metal iodides as photoconductors for digital imaging L. Fornaro	155